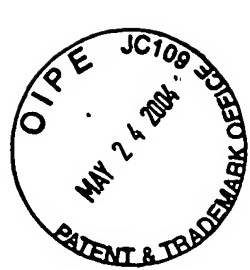
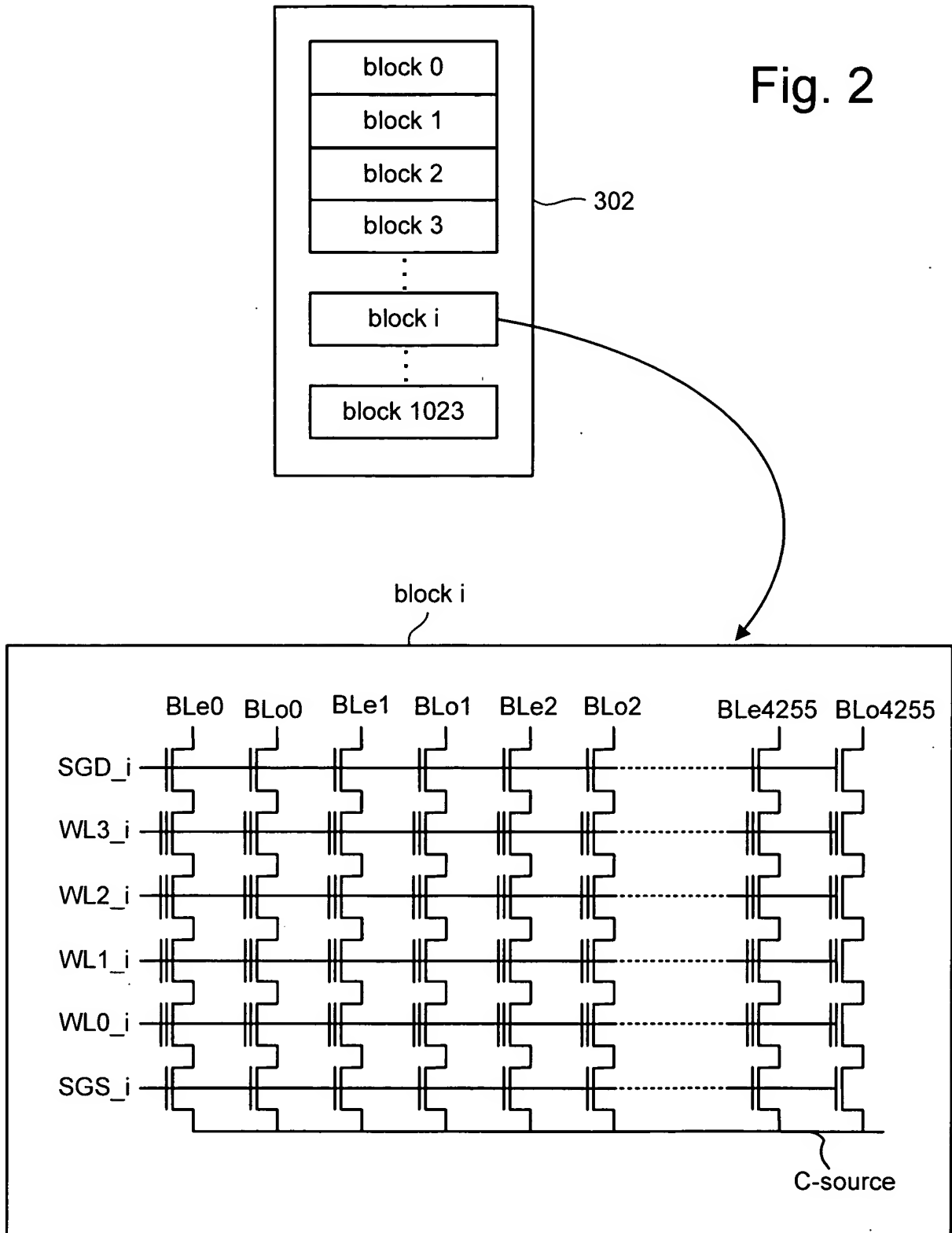


Fig. 1



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Phone: (415) 369-9660



[illegible]

Fig. 3



Fig. 4

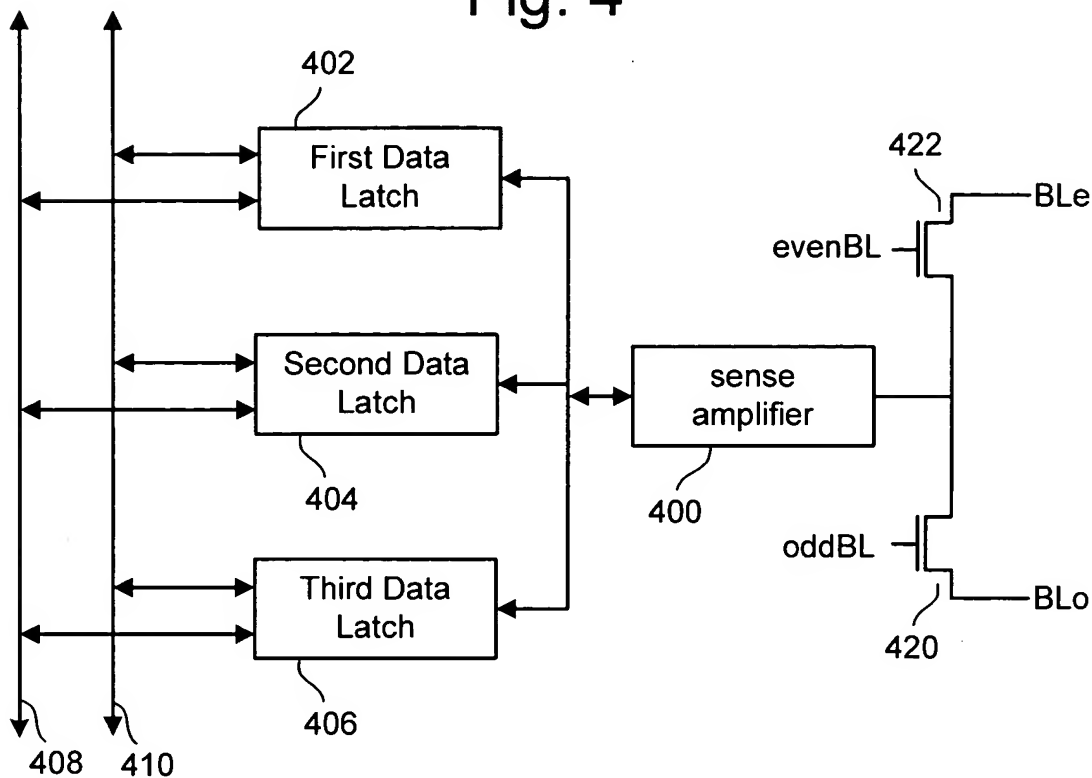
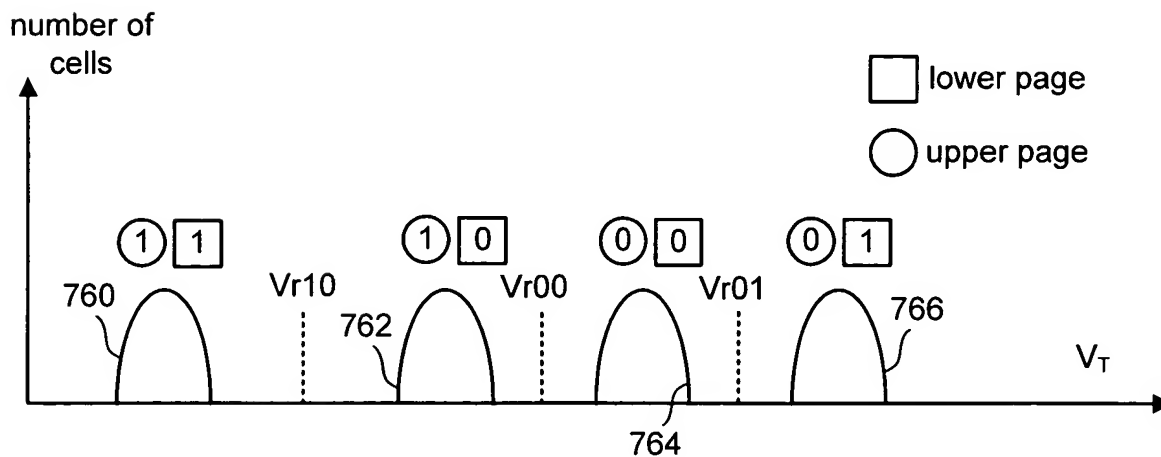


Fig. 5



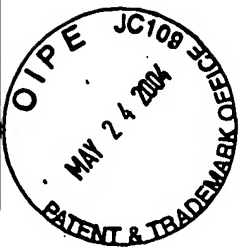


Fig. 6a

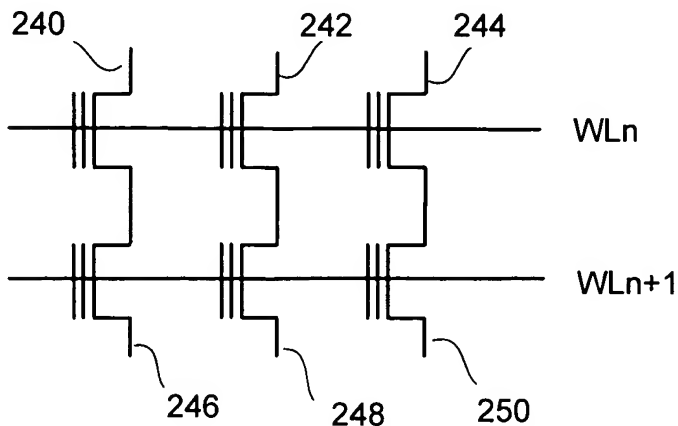


Fig. 6b

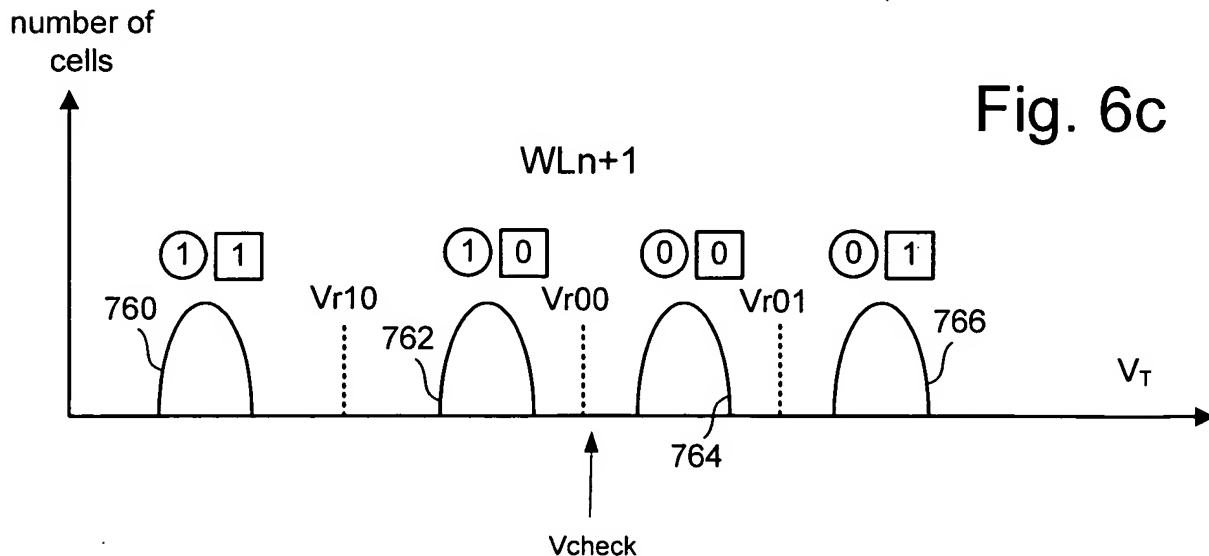
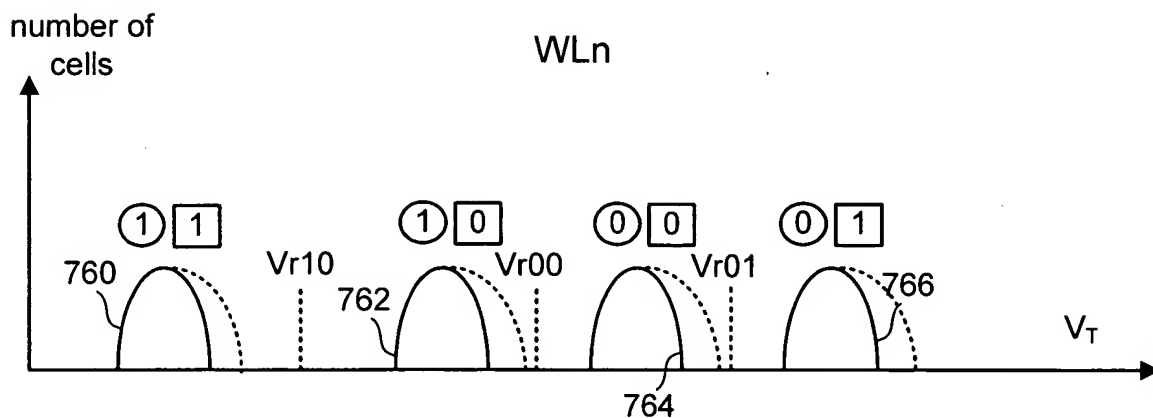
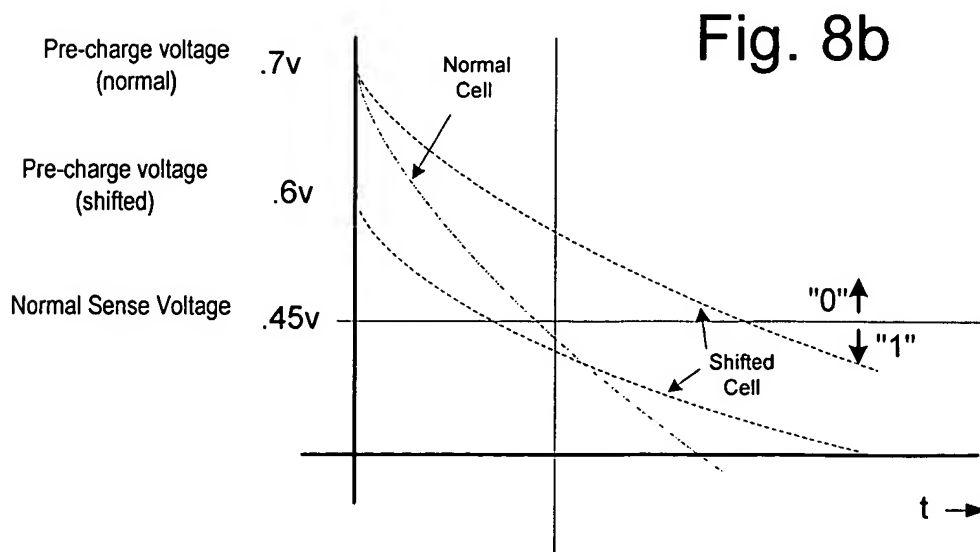
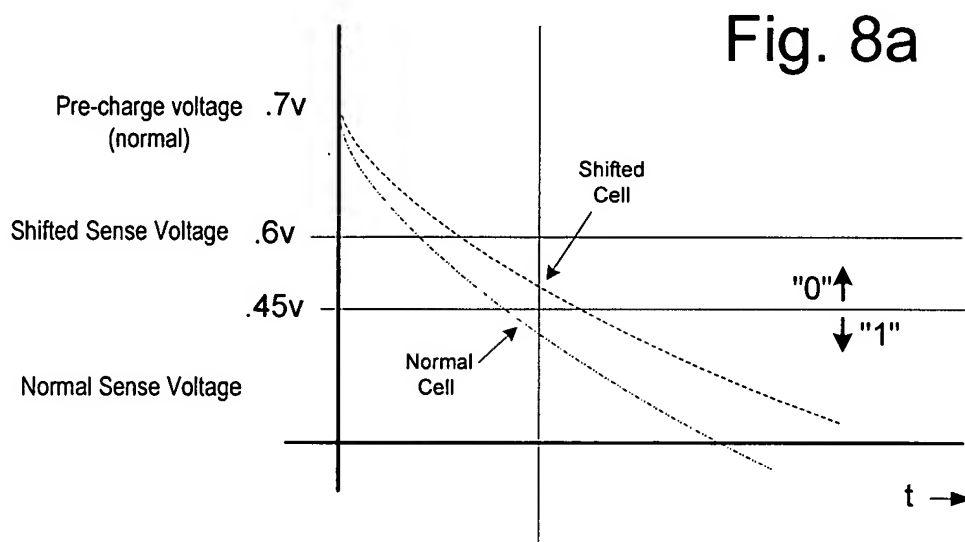
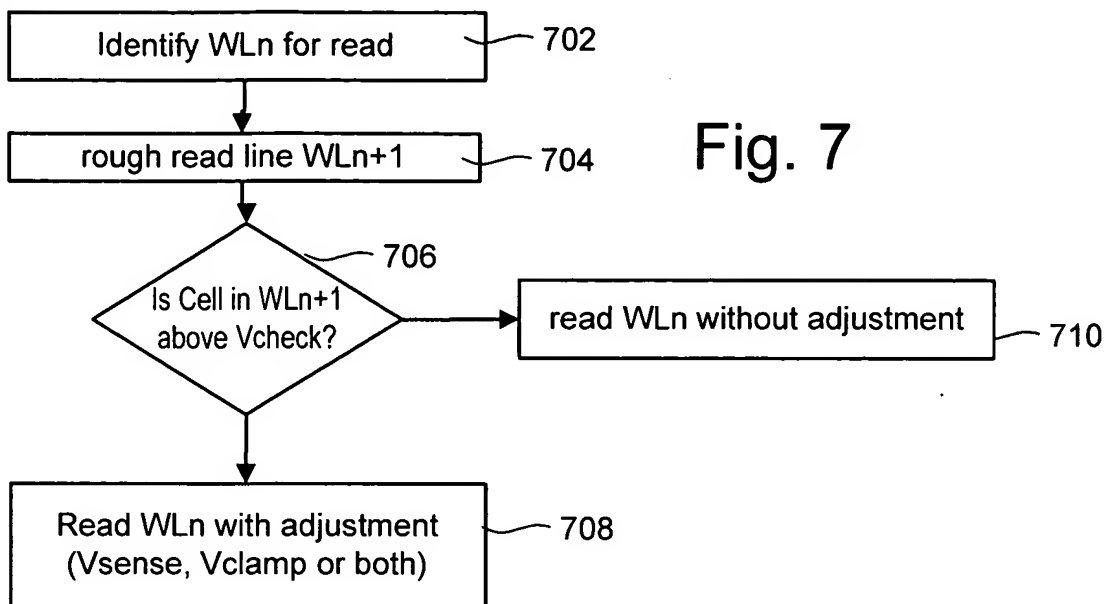
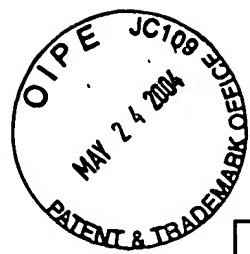


Fig. 6c



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Fig. 9

number of
cells

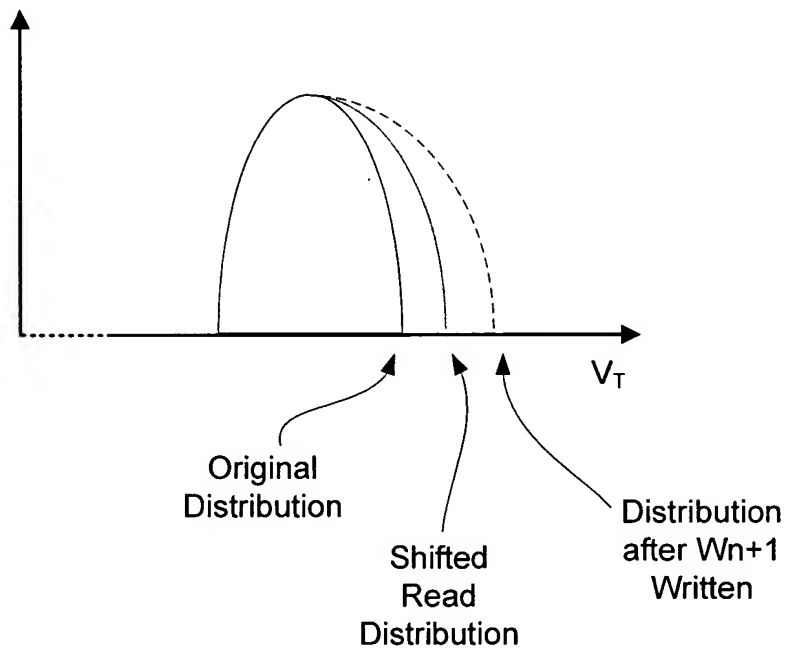


Figure 10b is a semi-logarithmic plot showing the relationship between current (pA) on the y-axis and voltage (mV) on the x-axis. The y-axis is logarithmic, ranging from 10^1 to 10^4 pA. The x-axis is linear, with markers for V_{r00} and V_{r01} . Three bell-shaped curves are plotted, corresponding to different clamp potentials (V_{Clamp}):

- $V_{\text{Clamp}} - 60\text{mv}$ (dotted line)
- $V_{\text{Clamp}} - 40\text{mv}$ (dash-dot line)
- $V_{\text{Clamp}} - 20\text{mv}$ (dashed line)
- V_{Clamp} (solid line)

The curves show that the peak current increases as the clamp potential becomes more negative.



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